

# **BTC12 SERIES**

# High-reliability discrete products and engineering services since 1977

### SILICON BIDIRECTIONAL THYRISTORS

#### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage <sup>(1)</sup>			
(T <sub>J</sub> = 125°C)			
BTC12-200	$V_{DRM}$	200	Volts
BTC12-400		400	
BTC12-600		600	
RMS on-state current ( $T_C = 70^{\circ}C$ )	I <sub>T(RMS)</sub>	12	Amps
Peak non-repetitive surge current			
(1 cycle, 50 Hz, t = 20ms)	I <sub>TSM</sub>	90	Amps
(1/2 cycle, 50Hz, t = 10ms)		100	
Circuit fusing considerations (T <sub>J</sub> = -40 to 125°C , t = 10ms)	I <sup>2</sup> t	40	A <sup>2</sup> s
Peak gate power (pulse width = 2.0μs)	P <sub>GM</sub>	16	Watts
Average gate power (t = 10ms)	P <sub>G(AV)</sub>	0.35	Watts
Peak gate current (pulse width = 1.0μs)	I <sub>GM</sub>	4.0	Amps
Operating junction temperature range	T,	-40 to +125	°C
Storage temperature range	T <sub>stg</sub>	-40 to +150	°C
Maximum rate of change of on-state current	di/dt		A /us
$(I_{TM} = 12A, I_G = 200mA)$	diyat	10	A/μs

Note 1: Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking capability such that the voltage applied exceeds the rated blocking voltage.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	Rejc	2.2	°C/W

### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур.	Max	Unit
Peak blocking current (either direction)					A
(Rated V <sub>DRM</sub> @ T <sub>J</sub> = 125°C, gate open)	I <sub>DRM</sub>	-	-	2.0	mA
Peak on-state voltage (either direction)	V				Volts
(I <sub>TM</sub> = 17A peak)	V <sub>TM</sub>	-	1.4	1.65	VOILS
Peak gate trigger voltage					
(main terminal voltage = 12V, $R_L$ = 100 $\Omega$ )					
All quadrants	$V_{GTM}$	-	-	2.5	Volts
(main terminal voltage = rated $V_{DRM}$ , $R_L = 1k\Omega$ , $T_J = 125$ °C)					
All quadrants		0.2	-	-	
Holding current (either direction)					mA
(main terminal voltage= 12V, gate open, initiating current = 1.0A, $T_C$ = 25°C)	I <sub>H</sub>	-	-	50	IIIA
Latching current					
(main terminal voltage = 24V, gate trigger source = 15V, $100\Omega$ )					
MT2(+), G(+)	IL	-	-	100	mA
MT2(-), G(-)		-	-	100	
MT2(+), G(-)		-	-	200	



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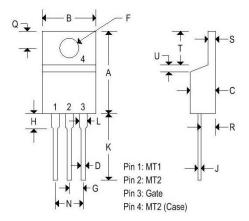
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Critical rate of rise of off state voltage (Rated V <sub>DRM</sub> , exponential voltage rise, gate open, T <sub>J</sub> = 125°C)	dv/dt	100	-	-	V/µs
Blocking voltage application rate (@ $T_C = 80^{\circ}C$ @ $V_{DRM}$ , $I_T = 6A$ , gate open, commutation di/dt = 4.3A/ms)	dv/dt(c)	5	-	-	V/µs

		QUADRANT			
Characteristic	Symbol	ı	н	Ш	IV
		mA	mA	mA	mA
Peak trigger current					
(main terminal voltage = 12V, $R_L = 100\Omega$ )					
BTC12-(), T <sub>J</sub> = 25°C	I <sub>GTM</sub>	50	50	50	80
BTC12-(), T <sub>J</sub> = -40°C		100	100	100	200

#### **MECHANICAL CHARACTERISTICS**

Case	TO-220AB
Marking	Alpha-numeric
Pin out	See below



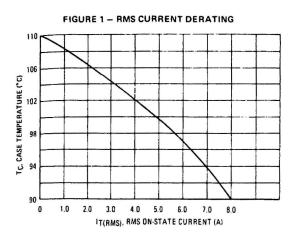
	TO-220AB				
	Inc	hes	Millimeters		
	Min	Max	Min	Max	
Α	0.575	0.620	14.600	15.750	
В	0.380	0.405	9.650	10.290	
С	0.160	0.190	4.060	4.820	
D	0.025	0.035	0.640	0.890	
F	0.142	0.147	3.610	3.730	
G	0.095	0.105	2.410	2.670	
Н	0.110	0.155	2.790	3.930	
J	0.014	0.022	0.360	0.560	
K	0.500	0.562	12.700	14.270	
L	0.045	0.055	1.140	1.390	
N	0.190	0.210	4.830	5.330	
Q	0.100	0.120	2.540	3.040	
R	0.080	0.110	2.040	2.790	
S	0.045	0.055	1.140	1.390	
T	0.235	0.255	5.970	6.480	
U	-	0.050	197	1.270	
٧	0.045	(2)	1.140	-	
Z		0.080	121	2.030	

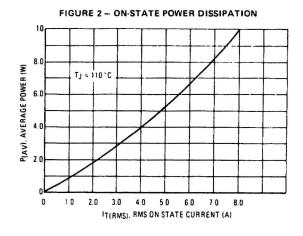


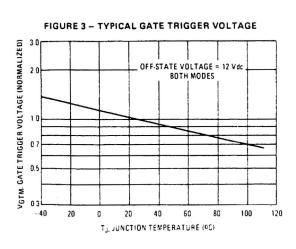
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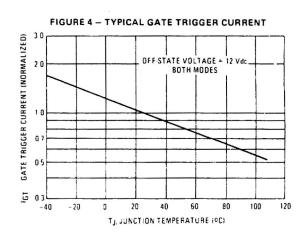
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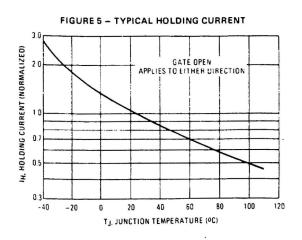
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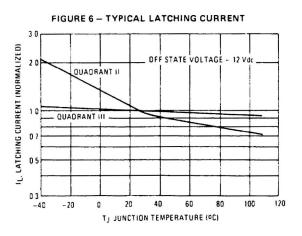










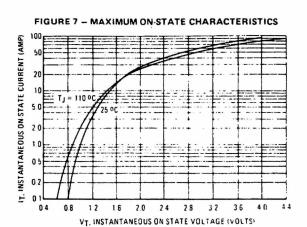




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### FIGURE 9 - TYPICAL THERMAL RESISTANCE FROM MOUNTING BASE TO HEATSINK

Metal to Metal:	Dry	0,9 °C!W
Metal to Metal:	Lubed	0,3 °C/W
With Insulator:	Dry	Not recommended
With Insulator:	Lubed	1,3 °C/W

These values are available when using the rectangular washer and mica insulator furnished for TO-220 Package. The recommended mounting torque is 0.68 Nm.

